



# 30V N-Channel MOSFETs

## General Description

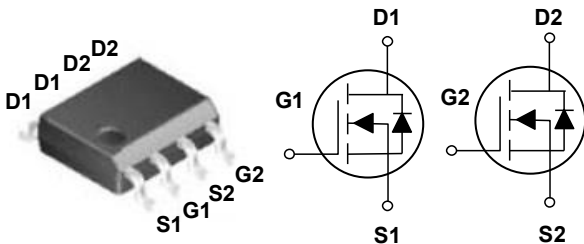
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
30 V	11 m $\Omega$	9 A

## Features

- $R_{DS(ON)} \leq 11m\Omega @ V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

SOP-8 Pin Configuration



## Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2<sup>nd</sup> SR

## Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current - Continuous ( $T_A=25^\circ\text{C}$ )	9	A
	Drain Current - Continuous ( $T_A=70^\circ\text{C}$ )	7.2	A
$I_{DM}$	Drain Current - Pulsed (NOTE 1)	36	A
$P_D$	Power Dissipation ( $T_A=25^\circ\text{C}$ )	1.47	W
	Power Dissipation - Derate above $25^\circ\text{C}$	0.01	W/ $^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
Marking Code		NC011	

## Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	85	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)****Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	---	11	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	---	---	15	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.5	V
gfs	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =8A	---	30	---	S

**Dynamic and switching Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =1A	---	23.2	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3.2	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.7	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =10V, V <sub>GS</sub> =10V, R <sub>GEN</sub> =2.7Ω, I <sub>D</sub> =30A	---	7	---	nS
T <sub>r</sub>	Rise Time		---	76.6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	27.1	---	
T <sub>f</sub>	Fall Time		---	52.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1MHz	---	1180	---	pF
C <sub>oss</sub>	Output Capacitance		---	177	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	132	---	
R <sub>g</sub>	Gate resistance		V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	3.2	

**Drain-Source Diode Characteristics and Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	9	A
I <sub>SM</sub>	Pulsed Source Current (NOTE 3)		---	---	18	A
V <sub>SD</sub>	Diode Forward Voltage (NOTE 3)	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

**NOTES :**

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.



Characteristics Curves

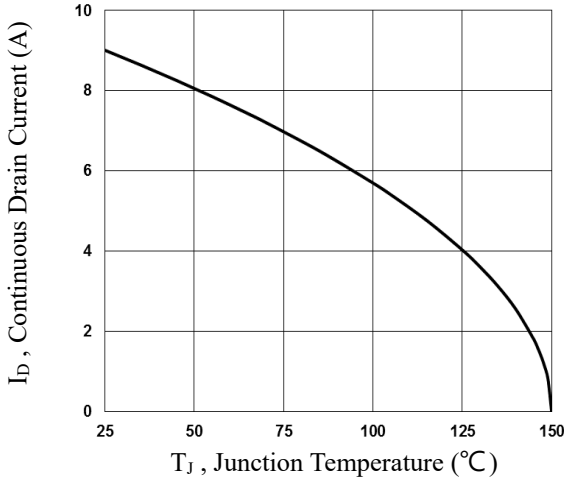


Fig.1 Continuous Drain Current vs.  $T_c$

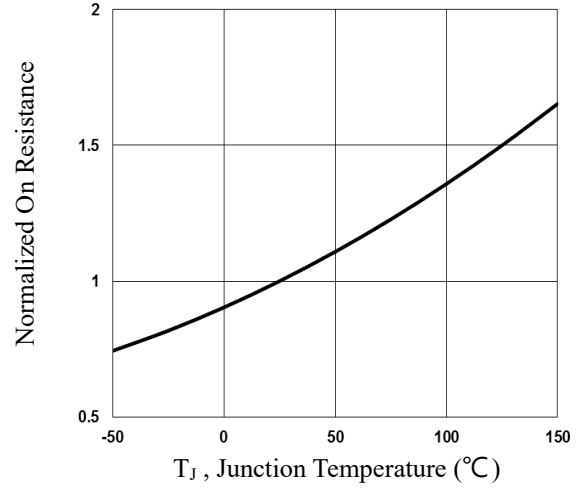


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$

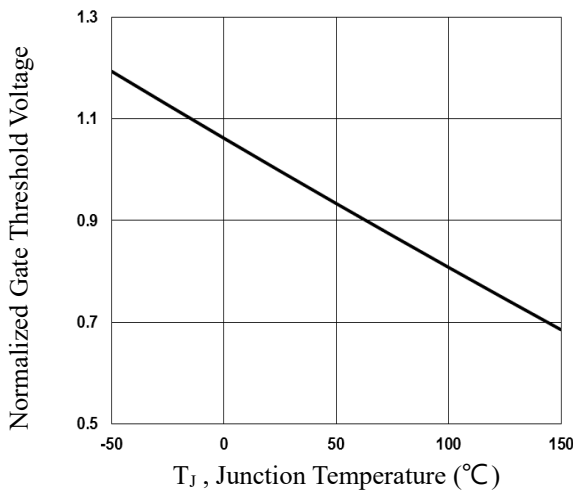


Fig.3 Normalized  $V_{th}$  vs.  $T_j$

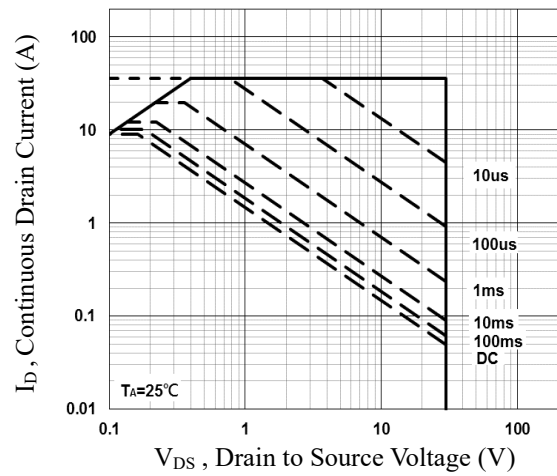


Fig.4 Maximum Safe Operation Area

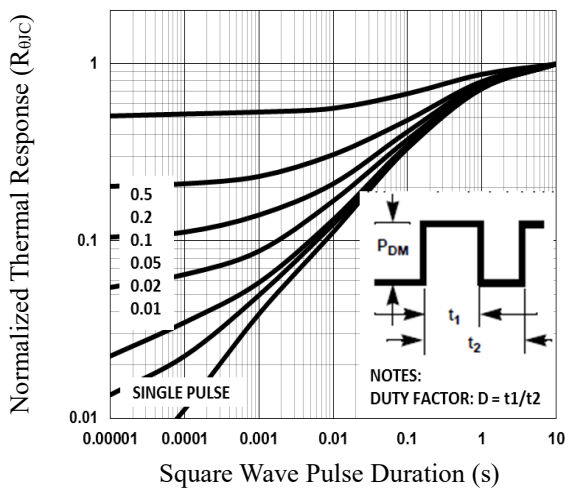


Fig.5 Normalized Transient Impedance

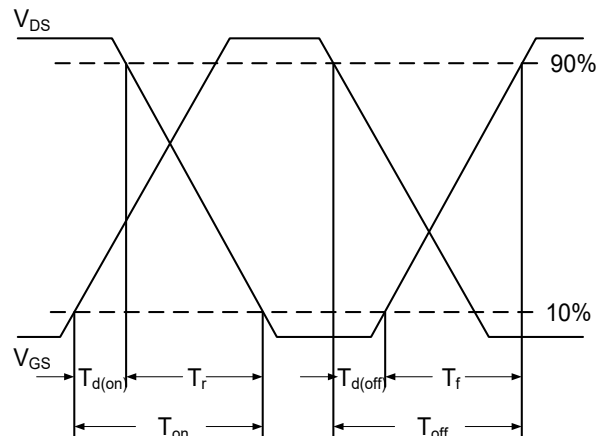


Fig.6 Switching Time Waveform



Characteristics Curves

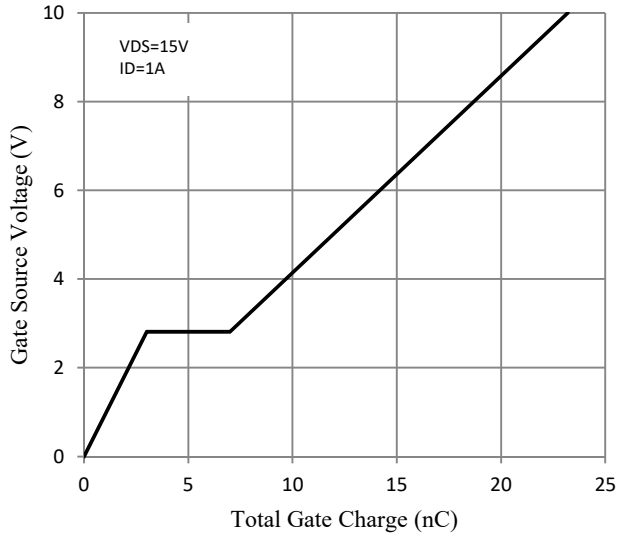
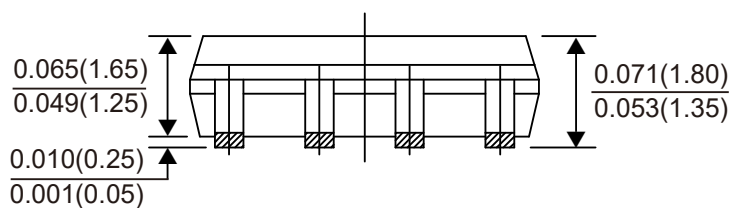
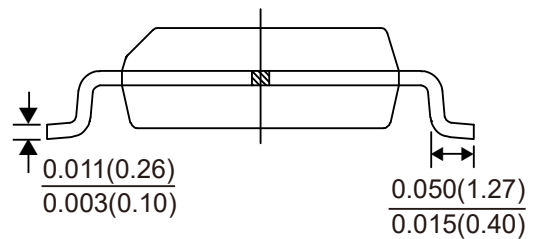
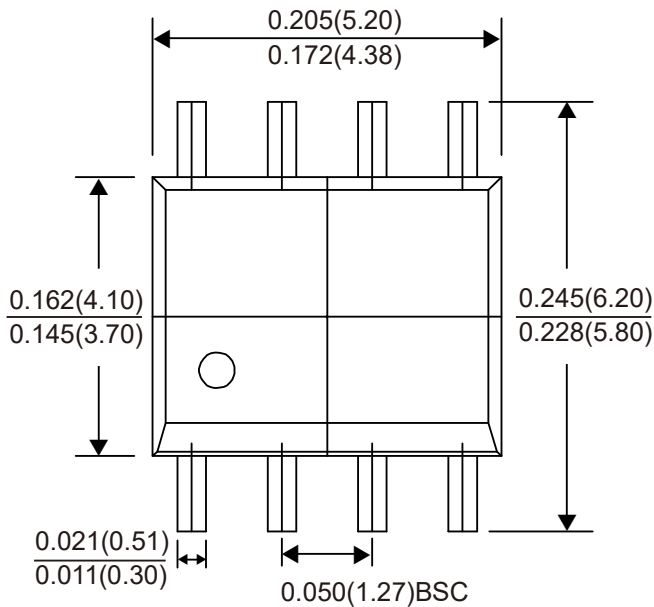


FIG. 7 Gate Charge Characteristics

Package Outline Dimensions



SOP-8

Dimensions in inches and (millimeters)



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